

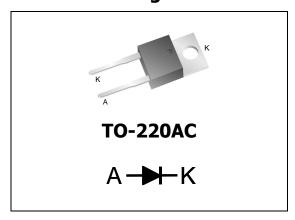


600 V, 10 A X-Series PFC Diode

## **Product Summary**

I <sub>F(AVG)</sub>	10	Α
$V_{RRM}$	600	V
Q <sub>RR</sub> (Typ at 125 °C)	94	nC
I <sub>RRM</sub> (Typ at 125 °C)	3.85	Α
Softness t <sub>B</sub> /t <sub>A</sub> (Typ at 125 °C)	0.5	

# **Pin Assignment**



# **RoHS Compliant**

Package uses Lead-free plating and Green mold compound.
Halogen free per IEC 61249-2-21.

## **General Description**

This device has the lowest  $Q_{RR}$  of any 600 V silicon diode. Its recovery characteristics increase efficiency, reduce EMI and eliminate snubbers.

# **Applications**

- Power Factor Correction (PFC) boost diode
- · Motor drive circuits
- DC-AC inverters

## **Features**

- Low Q<sub>RR</sub>, low I<sub>RRM</sub>, low t<sub>RR</sub>
- High dI<sub>F</sub>/dt capable (1000 A/μs)
- Soft recovery

## **Benefits**

- Increases efficiency
  - Eliminates need for snubber circuits
  - Reduces EMI filter component size and count
- Enables extremely fast switching

# **Absolute Maximum Ratings**

Absolute maximum ratings are the values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Symbol	Parameter	Conditions	Rating	Units
$V_{RRM}$	Peak repetitive reverse voltage		600	V
$I_{F(AVG)}$	Average forward current	T <sub>J</sub> = 150 °C, T <sub>C</sub> = 118 °C	10	Α
$I_{FSM}$	Non-repetitive peak surge current	60 Hz, 1/2 cycle	70	Α
$I_{FSM}$	Non-repetitive peak surge current	$1/2$ cycle of t = 28 $\mu$ s Sinusoid, $T_C$ = 25 °C	350	Α
$T_{J(MAX)}$	Maximum junction temperature		150	°C
T <sub>STG</sub>	Storage temperature		-55 to 150	°C
	Lead soldering temperature	Leads at 1.6 mm from case, 10 sec	300	°C
$P_D$	Power dissipation	T <sub>C</sub> = 25 °C	89	W

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## **Thermal Resistance**

Symbol	Resistance from:	Conditions	Rating	Units
$R_{\theta JC}$	Junction to case	TO-220AC	1.4	°C/W

# Electrical Specifications at $T_J = 25$ °C (unless otherwise specified)

			<u> </u>				
Symbol	Parameter	Conditions		Min	Тур	Max	Units
DC Chara	DC Characteristics						
I Davisina aviimant		$V_R = 600 \text{ V}, T_J = 25 ^{\circ}\text{C}$		-	-	250	μΑ
$I_R$	Reverse current	$V_R = 600 \text{ V}, T_J = 125 ^{\circ}$	V <sub>R</sub> = 600 V, T <sub>J</sub> = 125 °C		1.2	ı	mA
V	Forward voltage	$I_F = 10 \text{ A, } T_J = 25 ^{\circ}\text{C}$		- 2.4 3.0 V			
$V_{F}$	Forward voltage	$I_F = 10 \text{ A, } T_J = 150 ^{\circ}\text{C}$		-	2.1	-	V
$C_{J}$	Junction capacitance	V <sub>R</sub> = 10 V, 1 MHz		-	51	-	pF
Dynamic	Characteristics						
	Devenes reserves times	dI/dt = 200 A/μs	T <sub>J</sub> = 25 °C	-	23	-	ns
t <sub>RR</sub>	Reverse recovery time	$V_R = 400 \text{ V}, I_F = 10 \text{ A}$	T <sub>J</sub> = 125 °C	-	35	-	ns
	Devenue necessor de la mare	$dI/dt = 200 A/\mu s$	$T_{J} = 25  {}^{\circ}\text{C}$	-	36	54	nC
$Q_{RR}$	Reverse recovery charge	$V_R = 400 \text{ V}, I_F = 10 \text{ A}$	T <sub>J</sub> = 125 °C	-	94	-	nC
_	Maximum reverse	$dI/dt = 200 A/\mu s$	$T_J = 25$ °C	-	2.35	3.2	Α
$I_{RRM}$	recovery current	$V_R = 400 \text{ V}, I_F = 10 \text{ A}$	T <sub>J</sub> = 125 °C	-	3.85	-	Α
	c c t <sub>p</sub>	dI/dt = 200 A/μs	T <sub>J</sub> = 25 °C	-	0.75	-	
S	Softness factor = $\frac{t_B}{t_A}$	$V_R = 400 \text{ V}, I_F = 10 \text{ A}$	T <sub>J</sub> = 125 °C	-	0.5	-	

<u>Note to component engineers</u>: X-Series diodes employ Schottky technologies in their design and construction. Therefore, Component Engineers should plan their test setups to be similar to those for traditional Schottky test setups. (For additional details, see Application Note AN-300.)

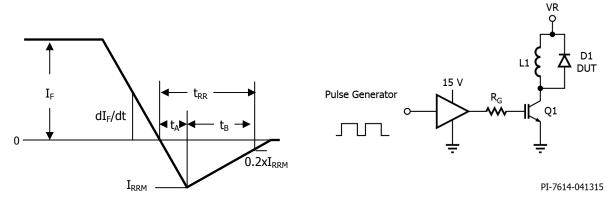
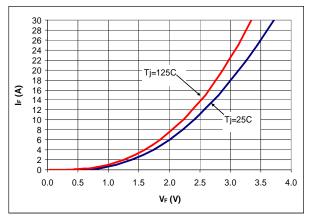


Figure 1. Reverse Recovery Definitions.

Figure 2. Reverse Recovery Test Circuit.

# Electrical Specifications at $T_1 = 25$ °C (unless otherwise specified)



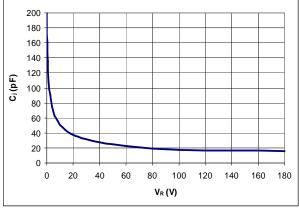
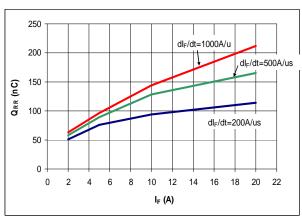


Figure 3. Typical I<sub>F</sub> vs. V<sub>F</sub>.

Figure 4. Typical C<sub>J</sub> vs. V<sub>R</sub>.



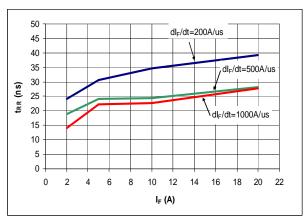
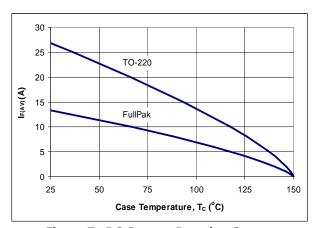


Figure 5. Typical  $Q_{RR}$  vs.  $I_F$  at  $T_J$  = 125 °.

Figure 6. Typical  $t_{RR}$  vs.  $I_F$  at  $T_J$  = 125 °C.



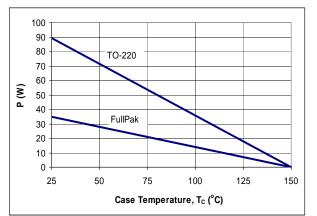


Figure 7. DC Current Derating Curve.

Figure 8. Power Derating Curve.

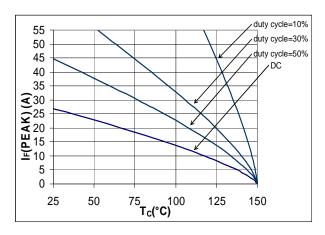


Figure 9.  $I_F(PEAK)$  vs.  $T_{Cr}$  f = 70 kHz, TO-220.

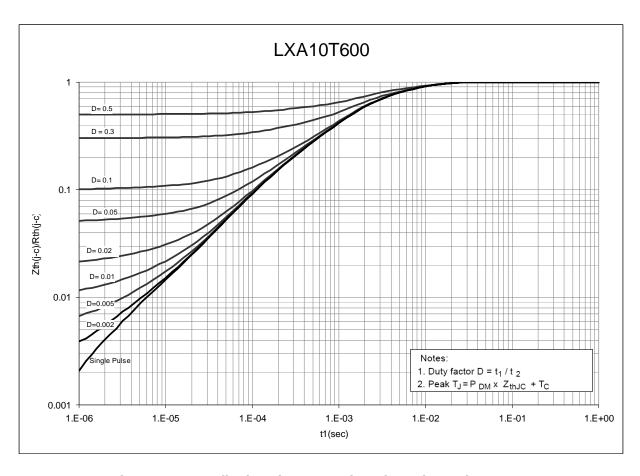
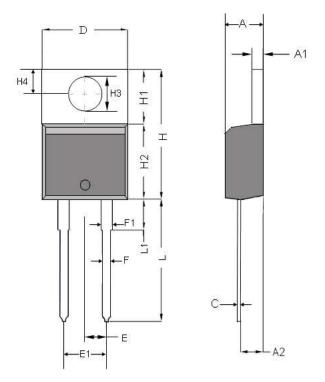


Figure 10. Normalized Maximum Transient Thermal Impedance, TO-220.

# **Dimensional Outline Drawings**



	Millimeters		
Dim	MIN	MAX	
Α	4.32	4.70	
<b>A1</b>	1.14	1.40	
A2	2.03	2.79	
С	0.34	0.610	
D	9.65	10.67	
E	2.49	2.59	
E1	4.98	5.18	
F	0.508	1.016	
F1	1.14	1.78	
Н	14.71	16.51	
H1	5.84	6.55	
H2	8.51	9.25	
Н3	3.53	3.96	
H4	2.54	3.05	
L	12.70	14.22	
L1	-	6.35	

## **TO-220AC**

<b>Mechanical Mounting Method</b>	Maximum Torque / Pressure specification
Screw through hole in package tab	1 Newton Meter (nm) or 8.8 inch-pounds (lb-in)
Clamp against package body	12.3 kilogram-force per square centimeter (kgf/cm²) or 175 lbf/in²

**Soldering time and temperature:** This product has been designed for use with high-temperature, lead-free solder. The component leads can be subjected to a maximum temperature of 300 °C, for up to 10 seconds. See Application Note AN-303, for more details.

# **Ordering Information**

Part Number	Package	Packing
LXA10T600	TO-220	50 units/tube

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## LXA10T600

Revision	Notes	
1.0	Released by Qspeed.	06/10
1.1	Converted to Power Integrations Document.	01/11
1.1	Stop Point of $t_{RR}$ error corrected due to typo in Figure 1.	11/13
1.2	Removed LXA10FP600 parts. Updated with new Brand Style.	01/16



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